

Abstract

Transistors including a buried channel layer intermediate to
a source and a drain and a surface layer intermediate to the
5 buried layer and a gate are operated so as to cause current
between the source and the drain to flow predominately through
the buried channel layer by applying a back-bias voltage to the
transistor. The back-bias voltage modulates a free charge
carrier density distribution in the buried layer and in the
10 surface layer.

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